

LS5018B LS5060B/LS5120B

 $\mathsf{TRISIL}^\mathsf{TM}$

FEATURES

- BIDIRECTIONAL CROWBAR PROTECTION.
- BREAKDOWN VOLTAGES RANGE: 18V, 60V and 120V.
- HOLDING CURRENT = 200mA min.
- HIGH SURGE CURRENT CAPABILITY IPP = 100A 10/1000 μs

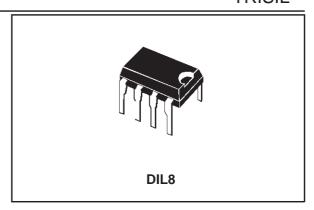
DESCRIPTION

The LS50xxB series has been designed to protect telecommunication equipment against lightning and transients induced by AC power lines.

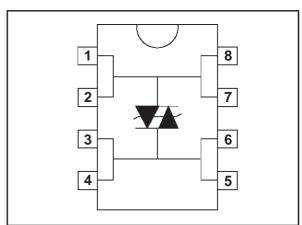
Its high surge current capability makes the LS50xxB a reliable protection device for very exposed equipment, or when series resistors are very low.

COMPLIES WITH THE FOLLOWING STANDARDS:

CCITT K17 - K20	10/700	μs	1.5 kV
	5/310	μs	38 A
VDE 0433	10/700	μs	2 kV
	5/200	μs	50 A
CNET	0.5/700	μs	1.5 kV
	0.2/310	μs	38 A



SCHEMATIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS (Tamb =25°C)

Symbol	Parameter	Value	Unit	
Ірр	Peak pulse current 10/1000 μs 8/20 μs		100 250	А
Ітѕм	Non repetitive surge peak on-state tp = 20 ms current		50	А
dl/dt	Critical rate of rise of on-state current Non repetitive		100	A/μs
dV/dt	Critical rate of rise of off-state voltage	5	kV/μs	
T _{stg} T _j	Storage and operating junction temperat	- 40 to + 150 150	°C °C	
TL	Maximum lead temperature for soldering	230	°C	

September 1998 Ed: 3A

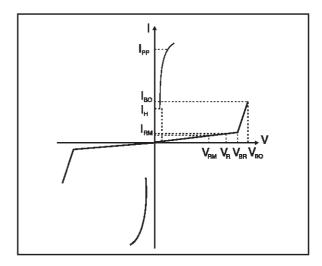
LS5018B/LS5060B/LS5120B

THERMAL RESISTANCE

Symbol	Parameter	Value	Unit
R _{th} (j-a)	Junction to ambient on printed circuit with recommended pad layout	80	°C/W

ELECTRICAL CHARACTERISTICS $(T_{amb} = 25^{\circ}C)$

Symbol	Parameter			
IRM	Leakage current at stand-offvoltage			
V _{RM}	Stand-offvoltage			
V_{BR}	Breakdownvoltage			
V _{BO}	Breakovervoltage			
lн	Holding current			
Іво	Breakovercurrent			
IPP	Peak pulse current			
С	Capacitance			

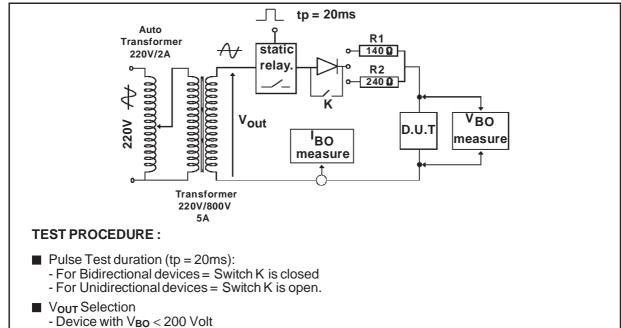


	I _{RM} @ V _{RM}		V _{BR} @ I _R		V _{BO}	@ I _{BO}	I _H	С
Type	max.		min.		max.	typ.	min.	max.
,					note 1		note 2	note 3
	μ Α	٧	٧	mA	V	mA	mA	pF
LS5018B	5	16	17	1	22	1300	200	150
LS5060B	10	50	60	1	85	1000	200	150
LS5120B	20	100	120	1	180	1250	250	150

Note 1 : Measured at 50Hz (1 cycle)
Note 2 : See test circuit
Note 3 : V_R = 5 V, F = 1MHz.

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TEST CIRCUIT 1 FOR I_{BO} and V_{BO} parameters:

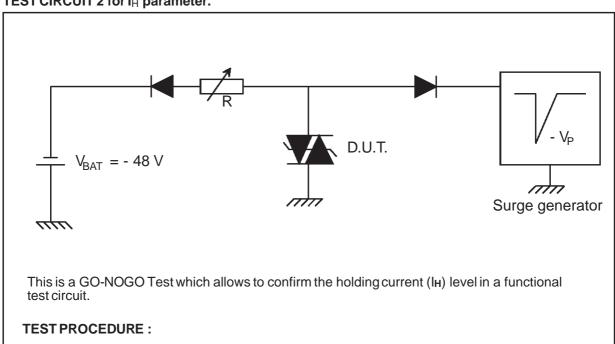


TEST CIRCUIT 2 for I_H parameter.

- Device with V_{BO} ≥ 200 Volt

- Vout = 250 V_{RMS}, R_1 = 140 Ω .

- Vout = 480 V_{RMS}, R_2 = 240 Ω .



■ 1) Adjust the current level at the I_H value by short circuiting the AK of the D.U.T.

2) Fire the D.U.T with a surge Current : Ipp = 10A, $10/1000 \mu s$. 3) The D.U.T will come back off-state within 50 ms max.

Figure 1 : Non repetitive surge peak current versus overload duration

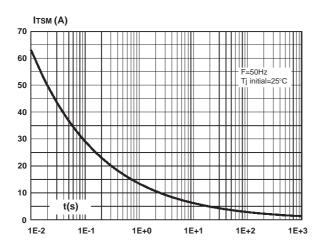


Figure 3: Relative variation of breakdown voltage versus ambient temperature.

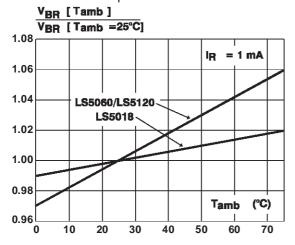


Figure 2: Relative variation of holding current versus junction temperature.

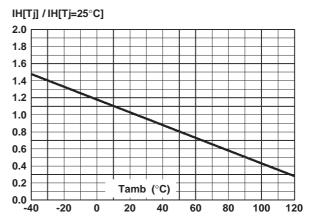
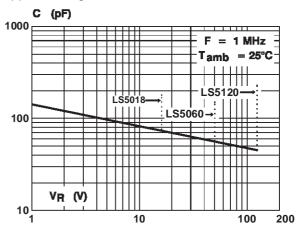
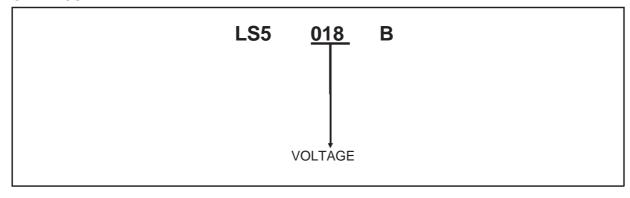


Figure 4: Junction capacitance versus reverse applied voltage.



ORDER CODE



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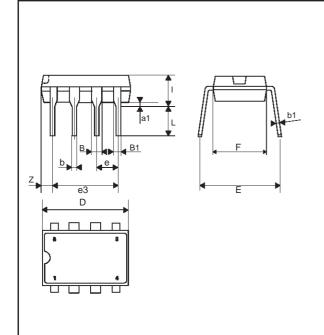
MARKING: Logo, Date Code, part Number.

Packaging: Products supplied in antistatic tubes.

Weight: 0.59g

PACKAGE MECHANICAL DATA

DIL 8 Plastic



	DIMENSIONS						
REF.	Millimetres Inches			;			
	Min.	Тур.	Max.	Min.	Тур.	Max.	
a1	0.70			0.027			
В	1.39		1.65	0.055		0.065	
B1	0.91		1.04	0.036		0.041	
b		0.5			0.020		
b1	0.38		0.50	0.015		0.020	
D			9.80			0.385	
Е		8.8			0.346		
е		2.54			0.100		
e3		7.62			0.300		
F			7.1			0.280	
Ι			4.8			0.189	
L	·	3.3			0.130		
Z	0.44		1.60	0.017		0.063	

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